

FIG. 1

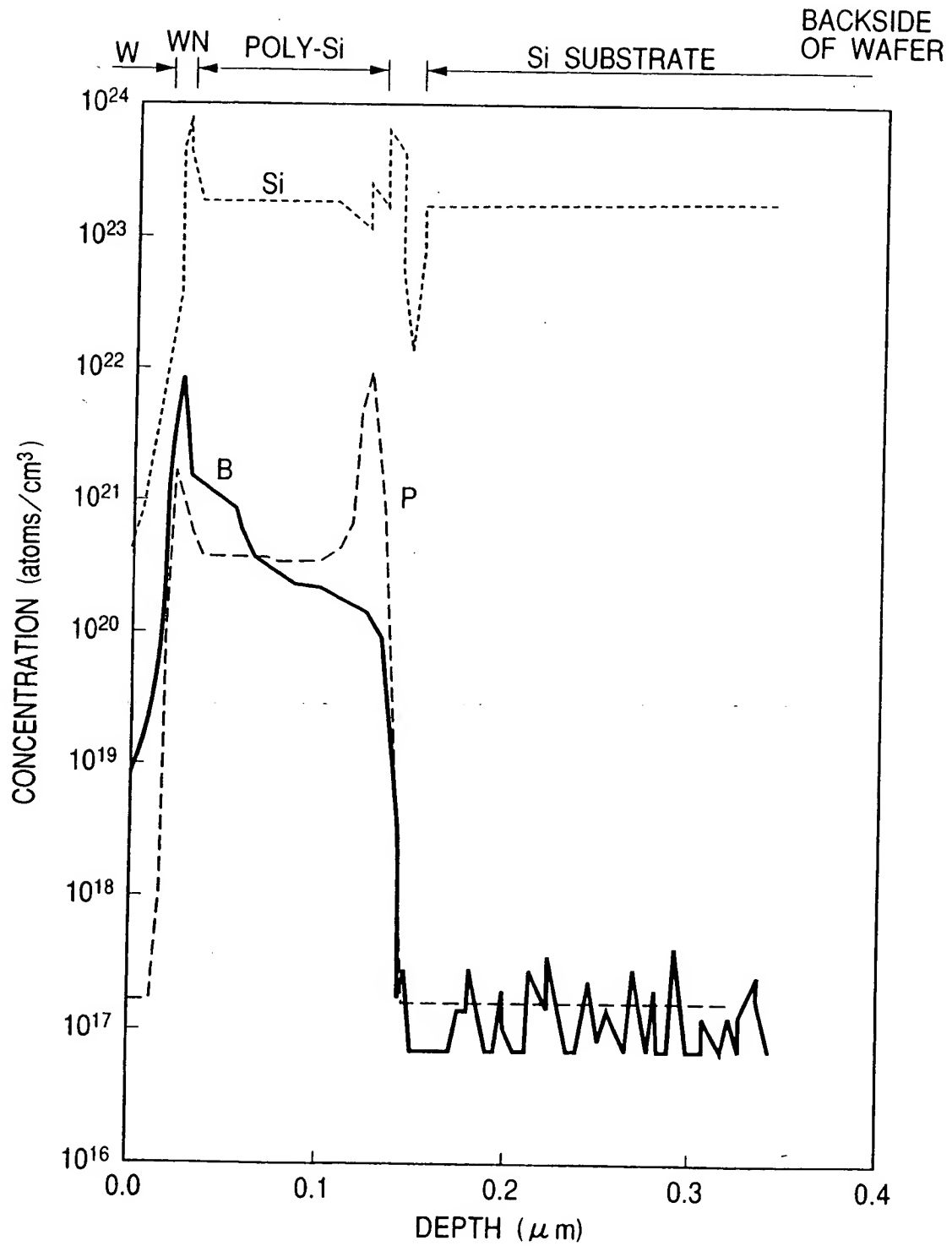
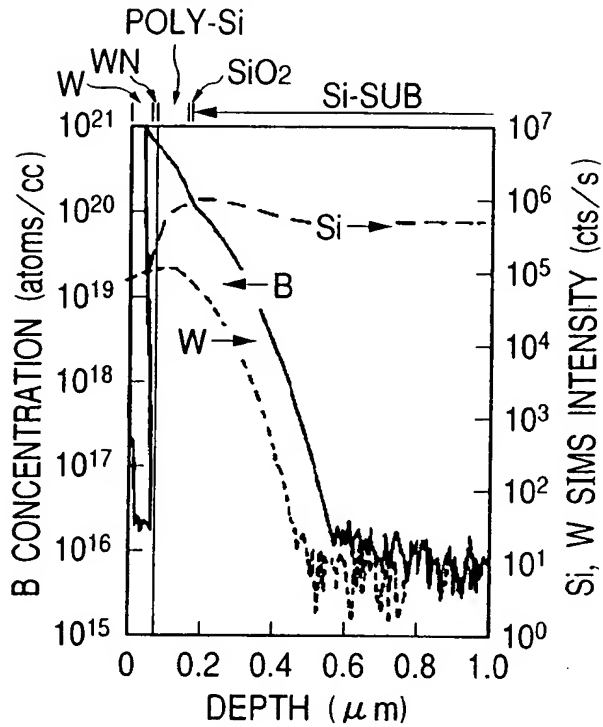
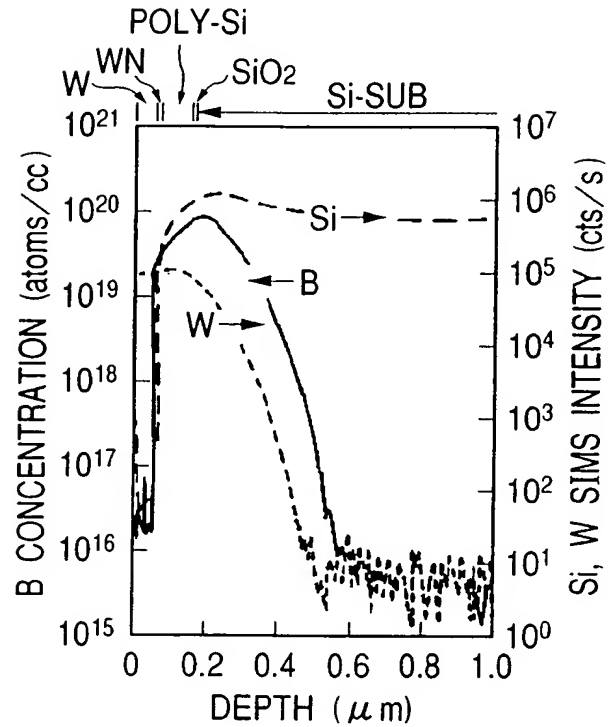


FIG. 2A

ANNEALING IN N₂,
900°C, 10min

**FIG. 2B**

ANNEALING IN H₂,
900°C, 10min

**FIG. 2C**

ANNEALING IN H₂
WITH 5% H₂O,
900°C, 10min

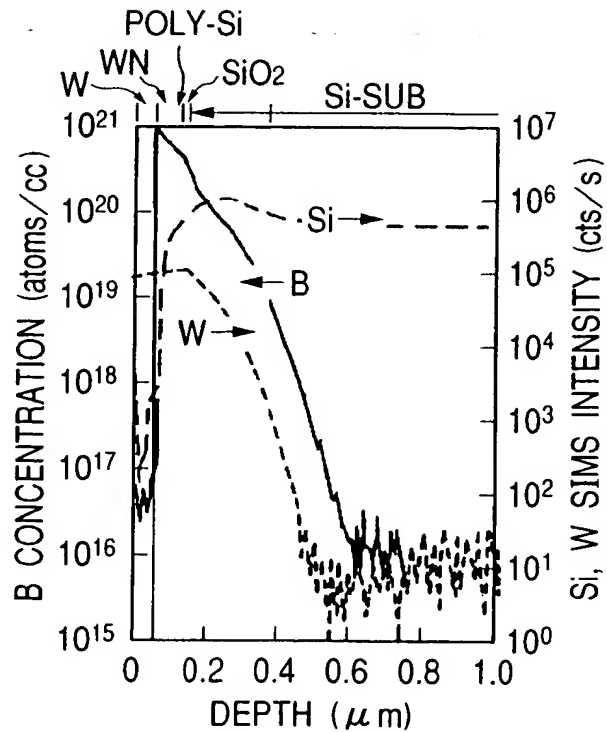


FIG. 3A

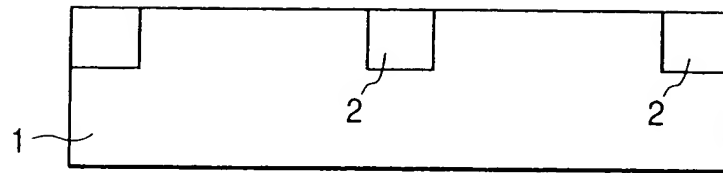


FIG. 3B

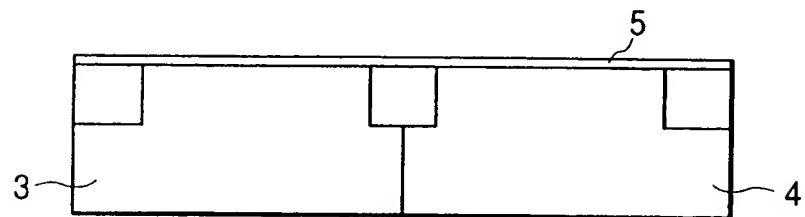


FIG. 3C

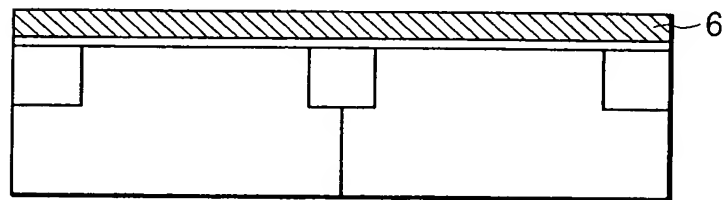


FIG. 3D

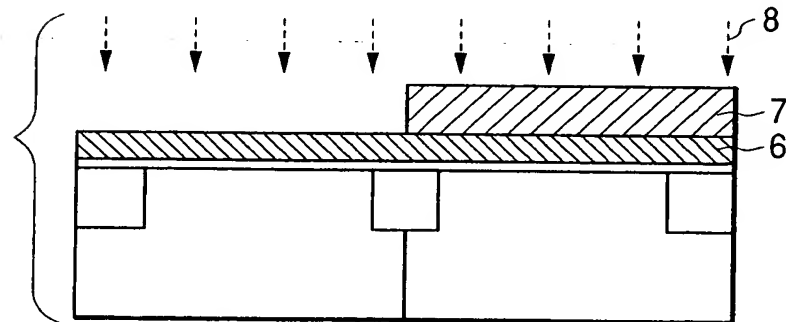


FIG. 3E

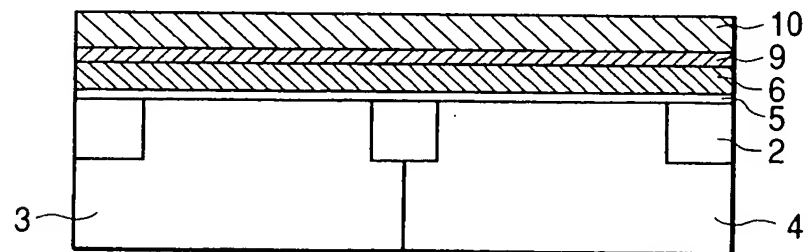


FIG. 4A

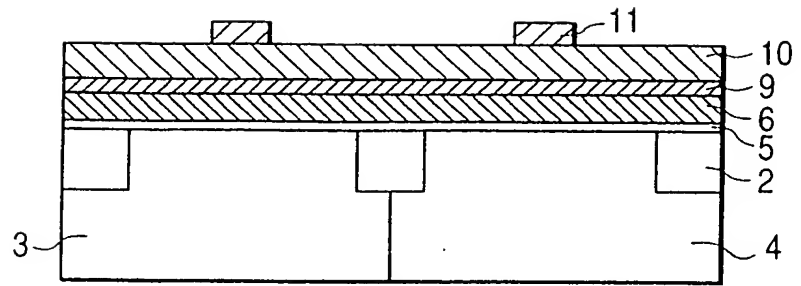


FIG. 4B

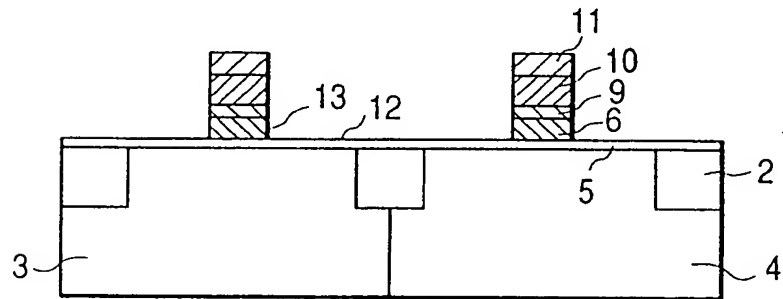


FIG. 4C

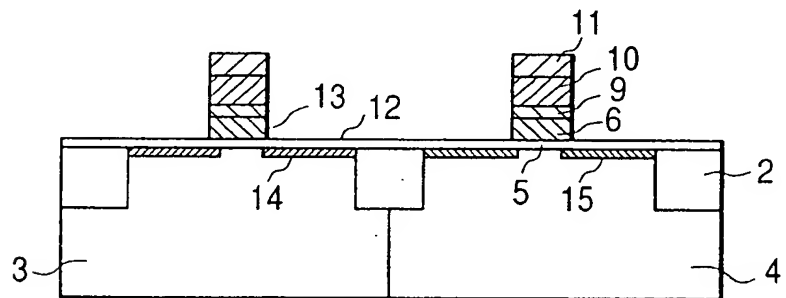


FIG. 4D

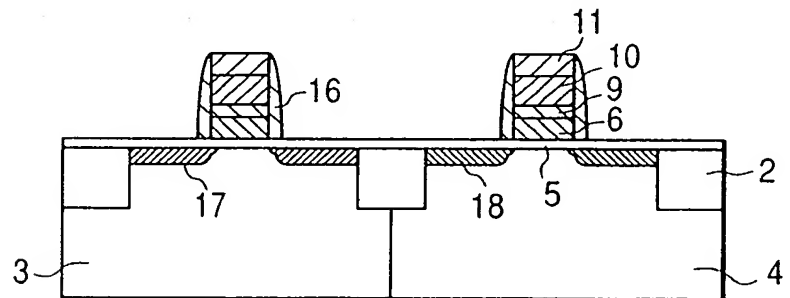


FIG. 4E

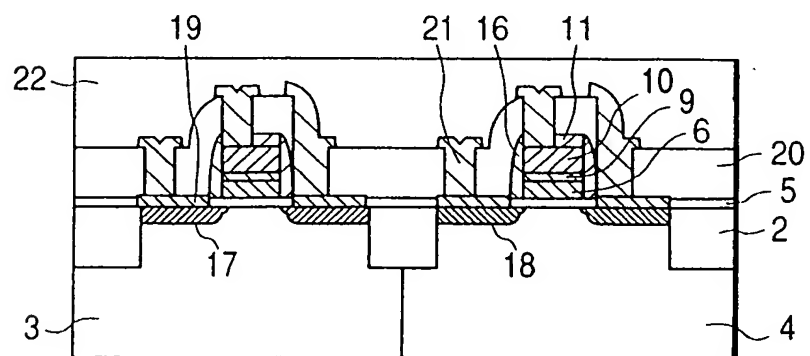
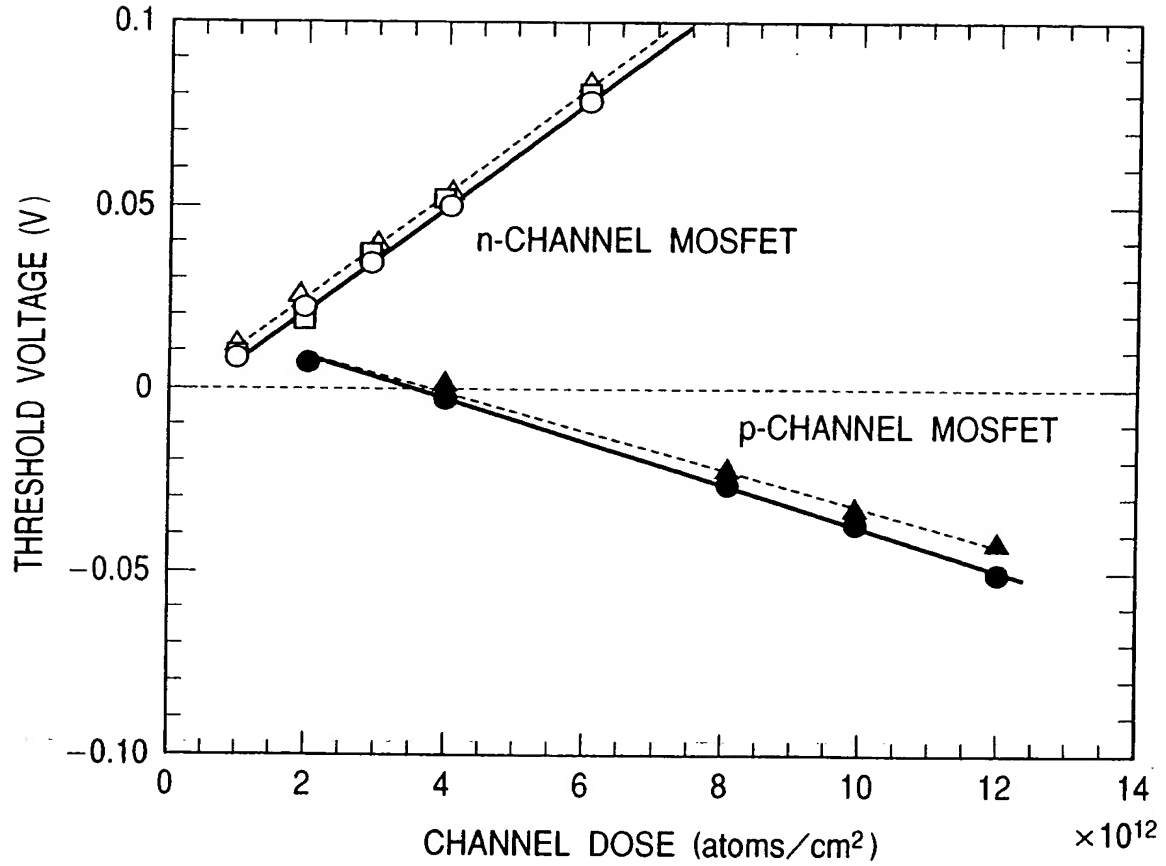


FIG. 5



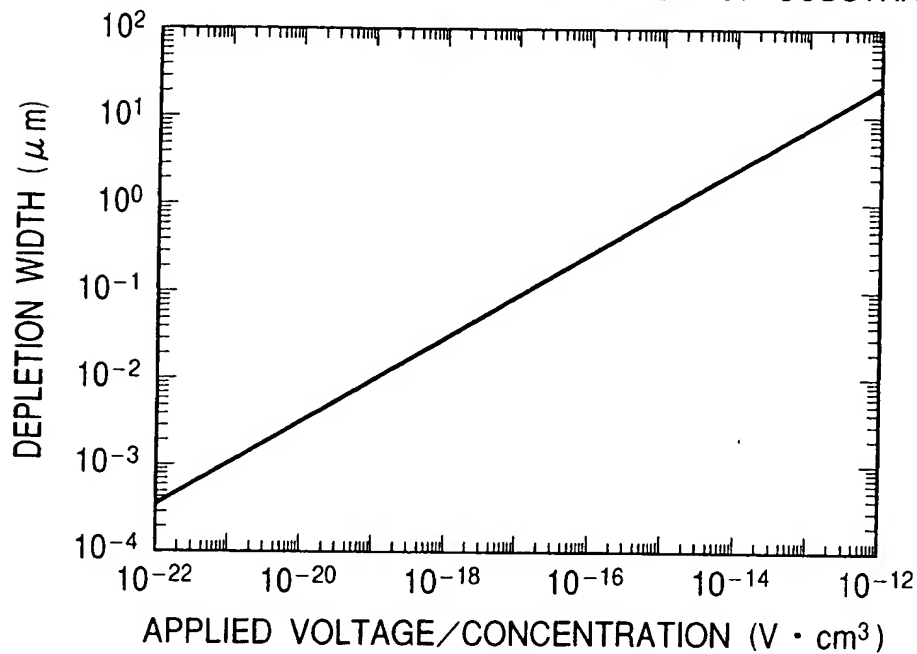
W/WN/POLY-Si GATE { ● p-CHANNEL MOSFET
(THIS WORK) { ○ n-CHANNEL MOSFET

W/WN/POLY-Si GATE { ▲ p-CHANNEL MOSFET
(PREVIOUS) { △ n-CHANNEL MOSFET

POLY-Si GATE (CONVENTIONAL) { □ n-CHANNEL MOSFET

FIG. 6A

RELATIONSHIP BETWEEN DEPLETION WIDTH AND
APPLIED VOLTAGE/CONCENTRATION OF SUBSTRATE

**FIG. 6B**

RELATIONSHIP BETWEEN BREAKDOWN VOLTAGE OF
pn JUNCTION AND CONCENTRATION OF SUBSTRATE

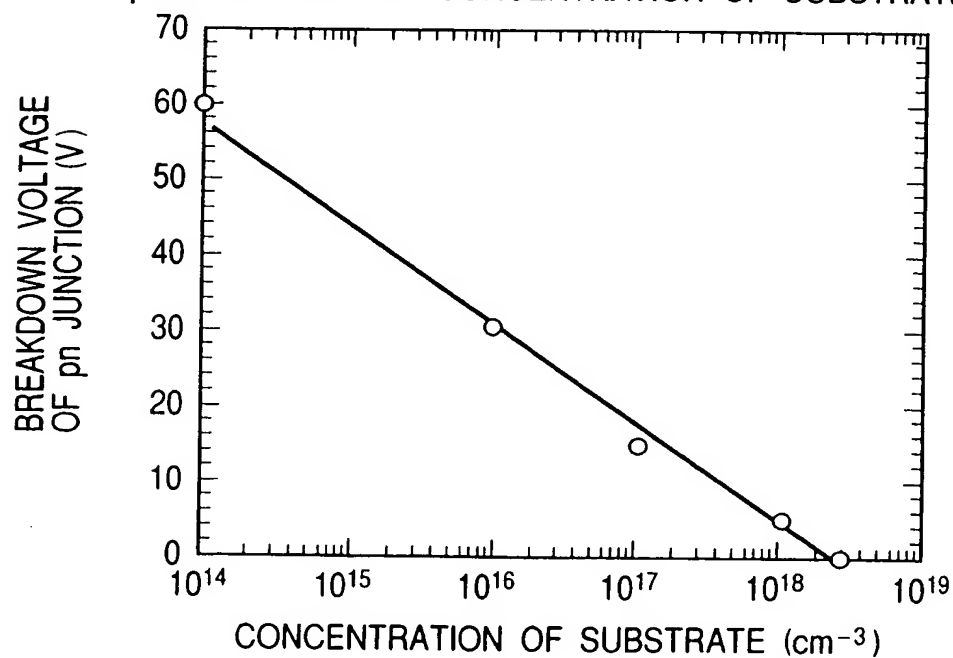


FIG. 7

